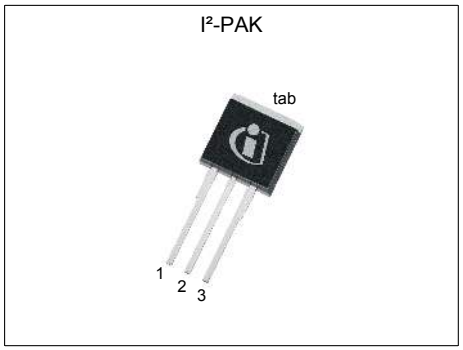
MOSFET

OptiMOS™5 Power-Transistor, 150 V



Features

- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- Very low reverse recovery charge (Q_{rr})
- 175 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC[1] for target application
- Ideal for high-frequency switching and synchronous rectification
- Halogen-free according to IEC61249-2-21

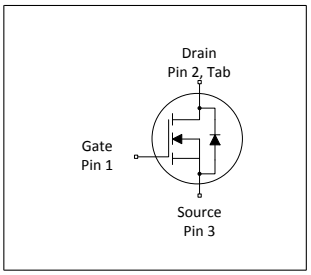


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	150	V
$R_{DS(on),max}$	7.6	mΩ
I_D	112	A
Q_{rr}	96	nC

Type / Ordering Code	Package	Marking	Related Links
IPI076N15N5	PG-TO262-3	076N15N5	-

[1] J-STD20 and JESD22

Table of Contents

1 Maximum ratings

at T_A=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	- -	- -	112 79	A	T_C=25 °C T_C=100 °C
Pulsed drain current[1]	$I_{D,pulse}$	-	-	448	A	T_C=25 °C
Avalanche energy, single pulse[2]	E_{AS}	-	-	130	mJ	I_D=100 A, R_{GS}=25 Ω
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	214	W	T_C=25 °C
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	0.4	0.7	K/W	-
Thermal resistance, junction - ambient, minimal footprint	R_{thJA}	-	-	62	K/W	-

3 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	150	-	-	V	V_{GS}=0 V, I_D=1 mA
Gate threshold voltage	$V_{GS(th)}$	3.0	3.8	4.6	V	V_{DS}=V_{GS}, I_D=160 µA
Zero gate voltage drain current	I_{DSS}	- -	0.1 10	1 100	µA	V_{DS}=120 V, V_{GS}=0 V, T_j=25 °C V_{DS}=120 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	1	100	nA	V_{GS}=20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	- -	5.9 6.4	7.6 8.4	mΩ	V_{GS}=10 V, I_D=56 A V_{GS}=8 V, I_D=28 A
Gate resistance[3]	R_G	-	1.1	1.7	Ω	-
Transconductance	g_{fs}	45	90	-	S	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=56 A

[1] See Diagram 3
[2] See Diagram 13
[3] Defined by design. Not subject to production test.

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance[1]	C_{iss}	-	3600	4700	pF	V_{GS}=0 V, V_{DS}=75 V, f=1 MHz
Output capacitance[1]	C_{oss}	-	900	1200	pF	V_{GS}=0 V, V_{DS}=75 V, f=1 MHz
Reverse transfer capacitance[1]	C_{rss}	-	21	37	pF	V_{GS}=0 V, V_{DS}=75 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	14	-	ns	V_{DD}=75 V, V_{GS}=10 V, I_D=56 A, $R_{G,ext}$=1.6 Ω
Rise time	t_r	-	4	-	ns	V_{DD}=75 V, V_{GS}=10 V, I_D=56 A, $R_{G,ext}$=1.6 Ω
Turn-off delay time	$t_{d(off)}$	-	20	-	ns	V_{DD}=75 V, V_{GS}=10 V, I_D=56 A, $R_{G,ext}$=1.6 Ω
Fall time	t_f	-	4	-	ns	V_{DD}=75 V, V_{GS}=10 V, I_D=56 A, $R_{G,ext}$=1.6 Ω

Table 6 Gate charge characteristics[2]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	21	-	nC	V_{DD}=75 V, I_D=56 A, V_{GS}=0 to 10 V
Gate to drain charge[1]	Q_{gd}	-	10	15	nC	V_{DD}=75 V, I_D=56 A, V_{GS}=0 to 10 V
Switching charge	Q_{sw}	-	17	-	nC	V_{DD}=75 V, I_D=56 A, V_{GS}=0 to 10 V
Gate charge total[1]	Q_g	-	49	61	nC	V_{DD}=75 V, I_D=56 A, V_{GS}=0 to 10 V
Gate plateau voltage	$V_{plateau}$	-	5.7	-	V	V_{DD}=75 V, I_D=56 A, V_{GS}=0 to 10 V
Output charge[1]	Q_{oss}	-	136	181	nC	V_{DD}=75 V, V_{GS}=0 V

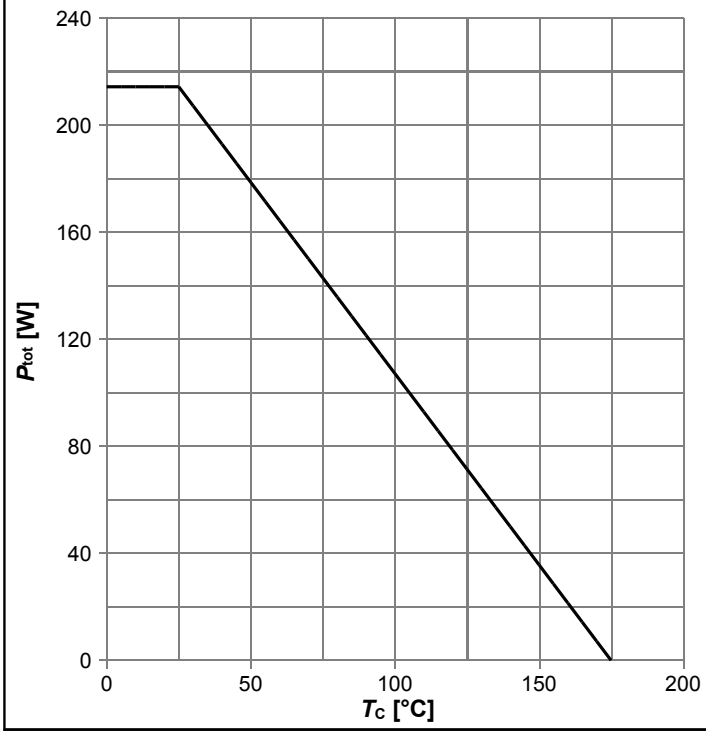
Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continous forward current	I_S	-	-	112	A	T_C=25 °C
Diode pulse current	$I_{S,pulse}$	-	-	448	A	T_C=25 °C
Diode forward voltage	V_{SD}	-	0.89	1.1	V	V_{GS}=0 V, I_F=56 A, T_j=25 °C
Reverse recovery time[1]	t_{rr}	-	69	138	ns	V_R=75 V, I_F=56 A, di_F/dt=100 A/µs
Reverse recovery charge[1]	Q_{rr}	-	96	192	nC	V_R=75 V, I_F=56 A, di_F/dt=100 A/µs

[1] Defined by design. Not subject to production test.
[2] See ″Gate charge waveforms″ for parameter definition

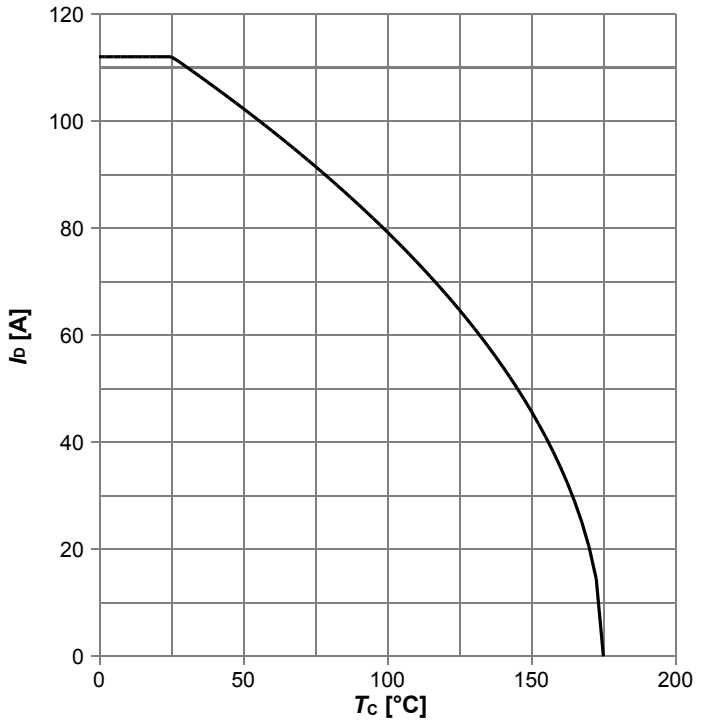
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



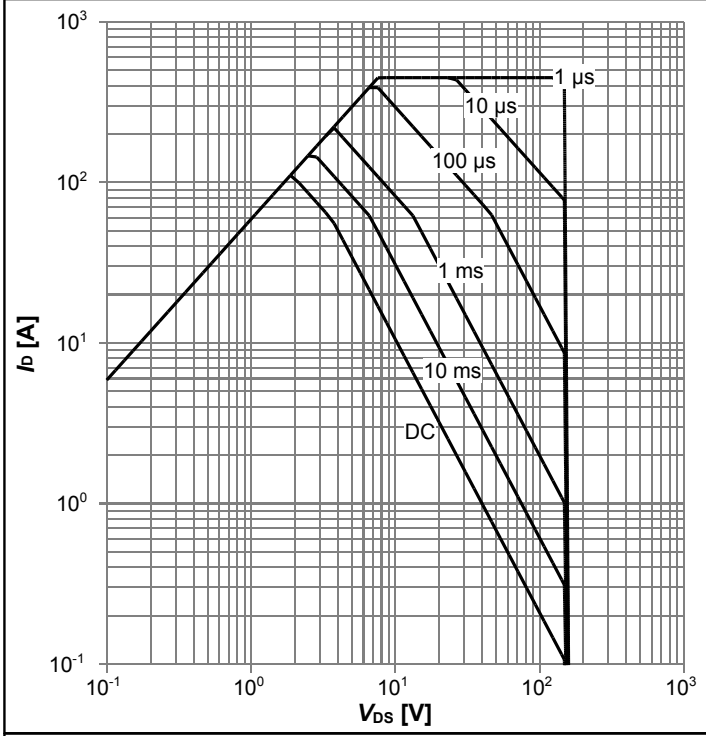
$P_{tot}=f(T_C)$

Diagram 2: Drain current



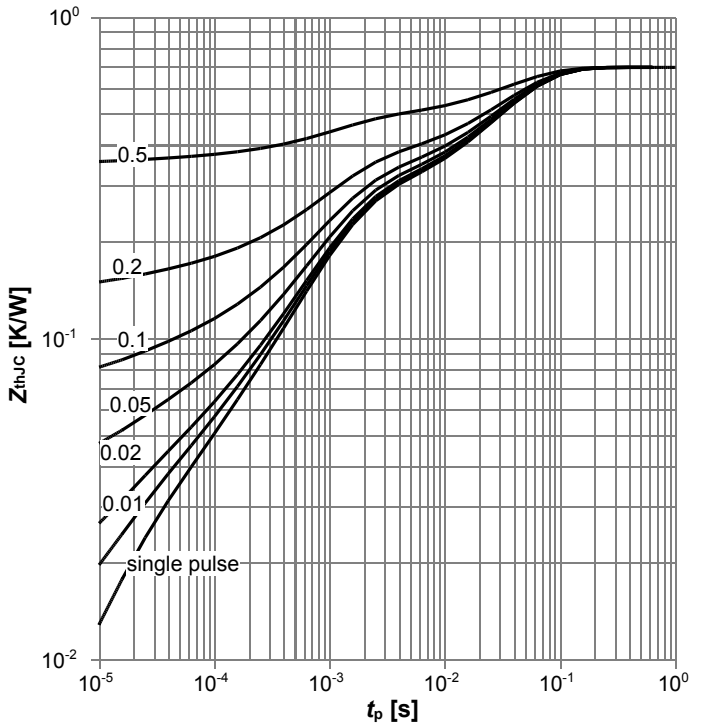
$I_D=f(T_C)$; $V_{GS}\geq 10$ V

Diagram 3: Safe operating area



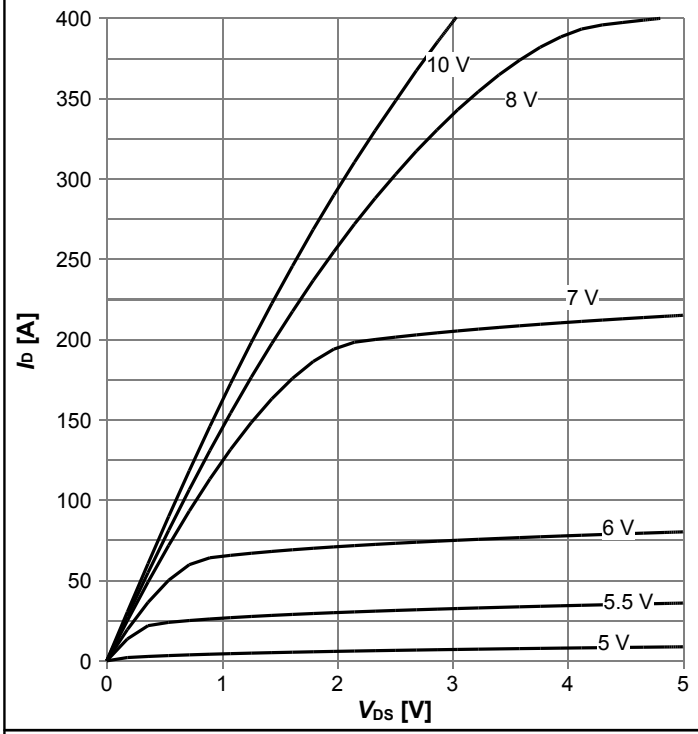
$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$; parameter: t_p

Diagram 4: Max. transient thermal impedance



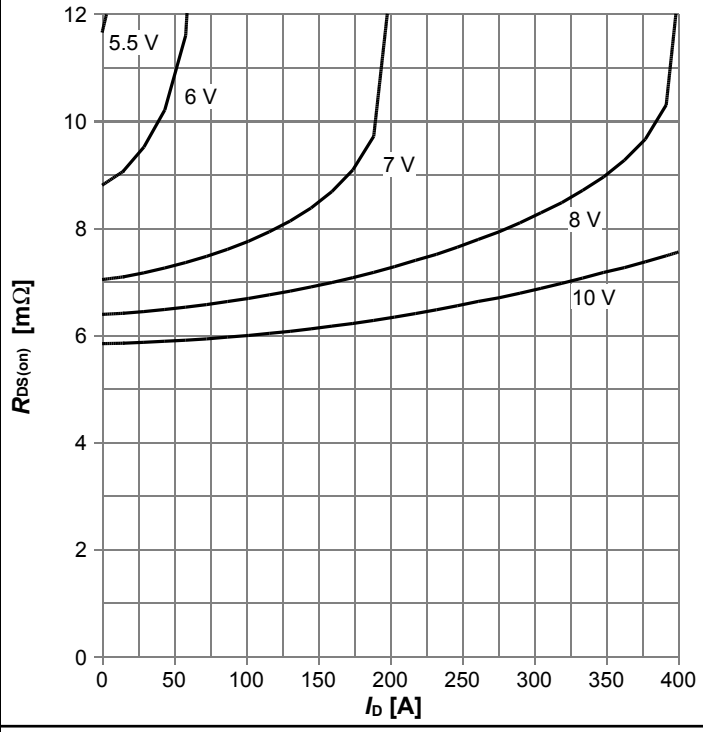
$Z_{thJC}=f(t_p)$; parameter: $D=t_p/T$

Diagram 5: Typ. output characteristics



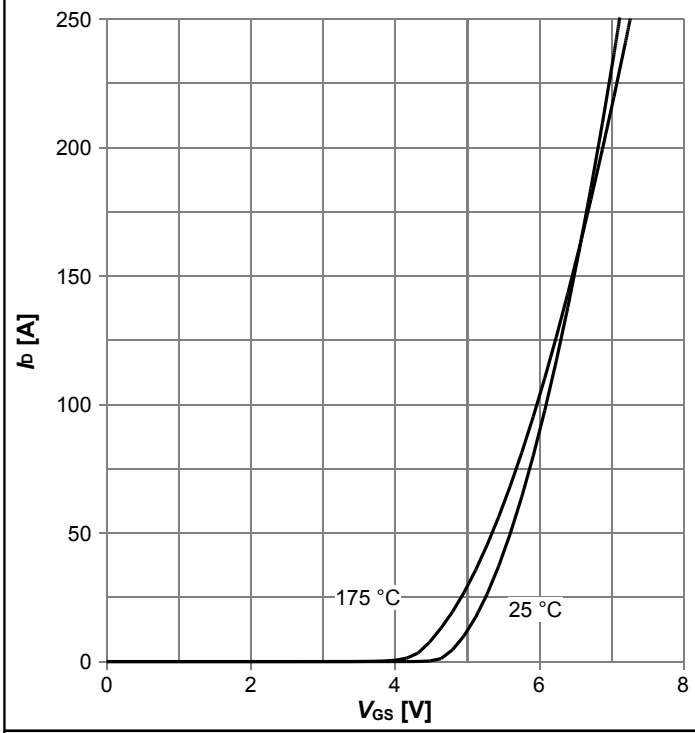
I_D=f(V_{DS}); T_j=25 °C; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



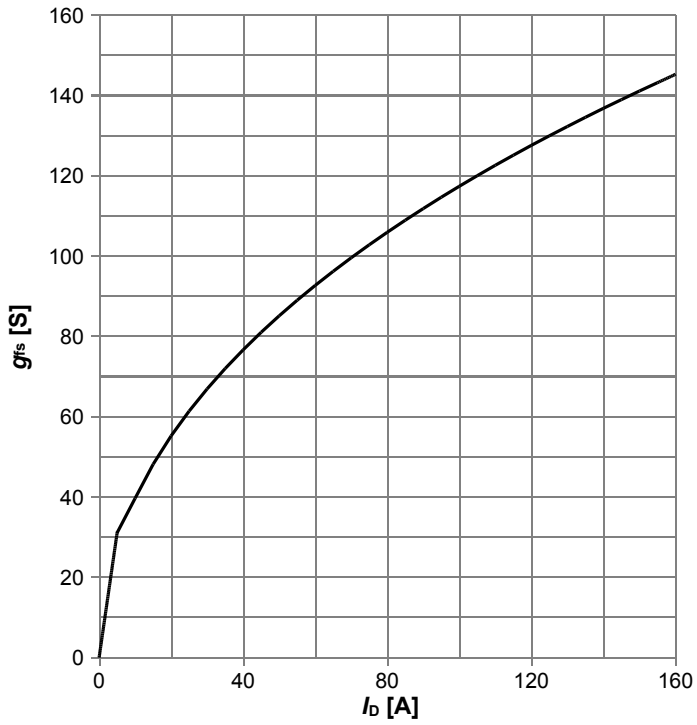
$R_{DS(on)}$=f(I_D); T_j=25 °C; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



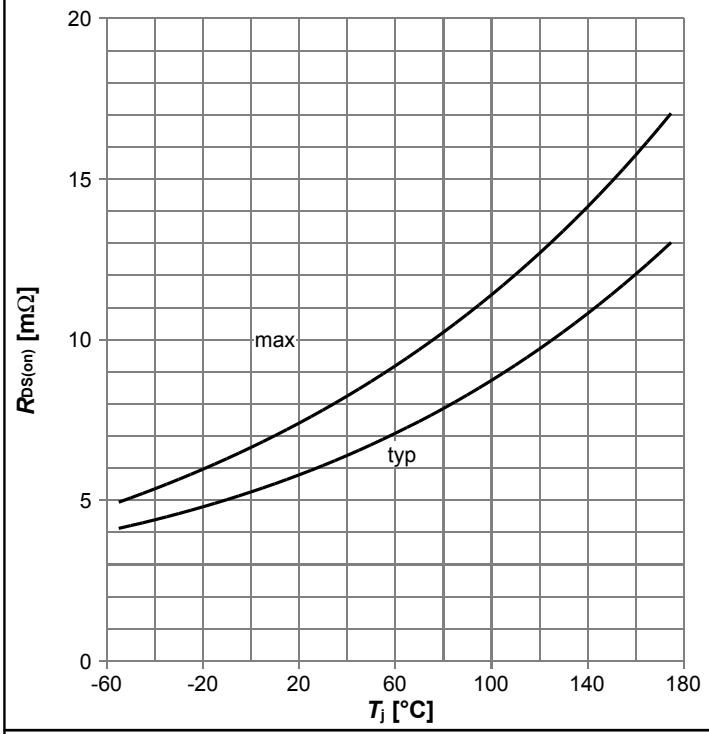
I_D=f(V_{GS}); |V_{DS}|>2|I_D|$R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. forward transconductance



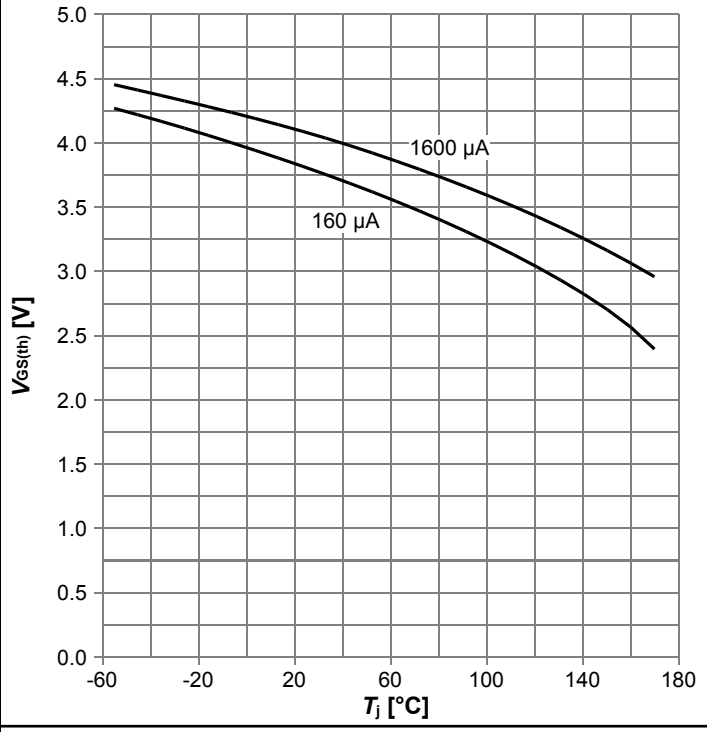
g_{fs}=f(I_D); T_j=25 °C

Diagram 9: Drain-source on-state resistance



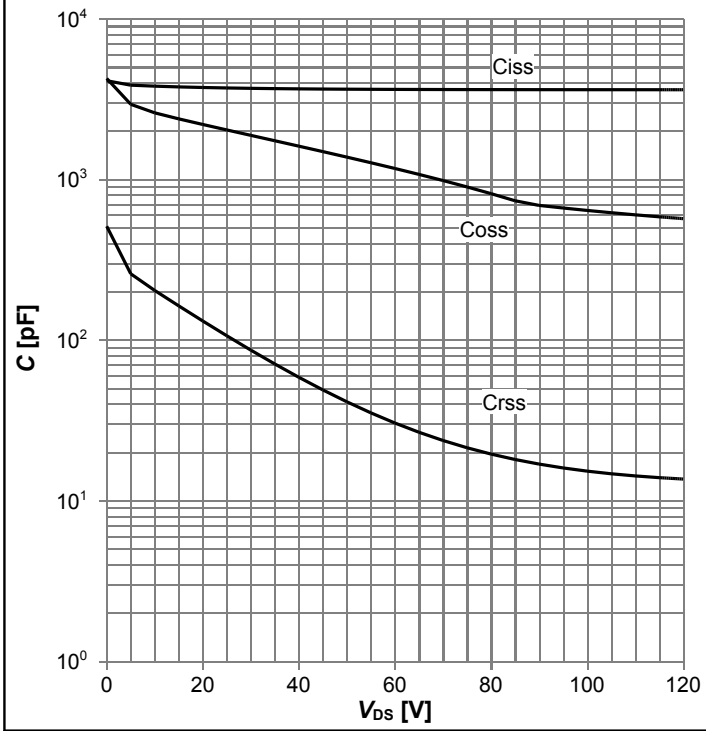
$R_{DS(on)}$=f(T_j); I_D=56 A; V_{GS}=10 V

Diagram 10: Typ. gate threshold voltage



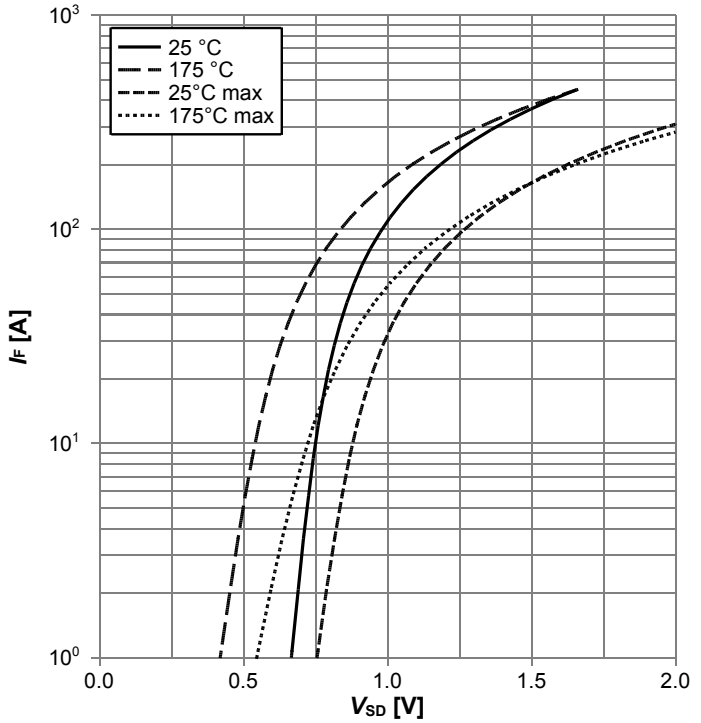
$V_{GS(th)}$=f(T_j); V_{GS}=V_{DS}; parameter: I_D

Diagram 11: Typ. capacitances



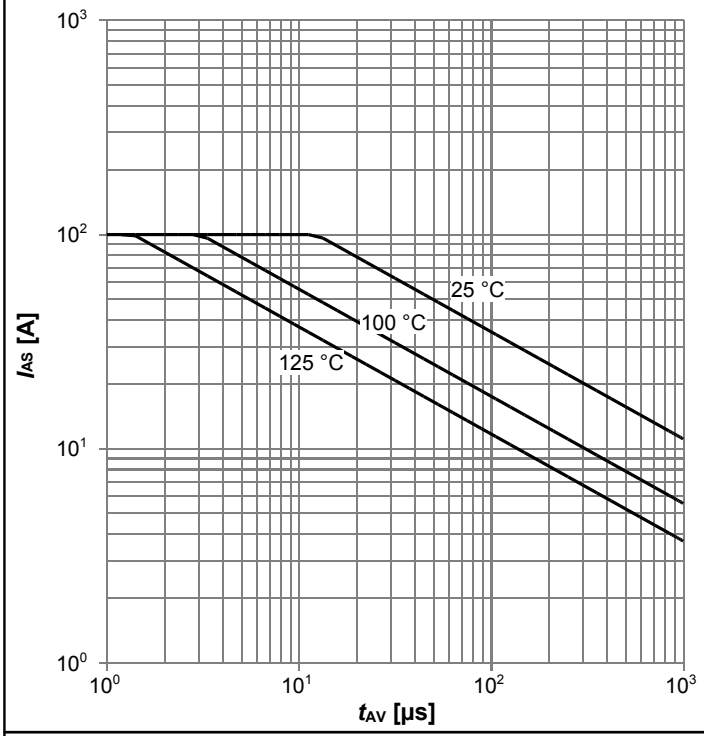
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Diagram 12: Forward characteristics of reverse diode



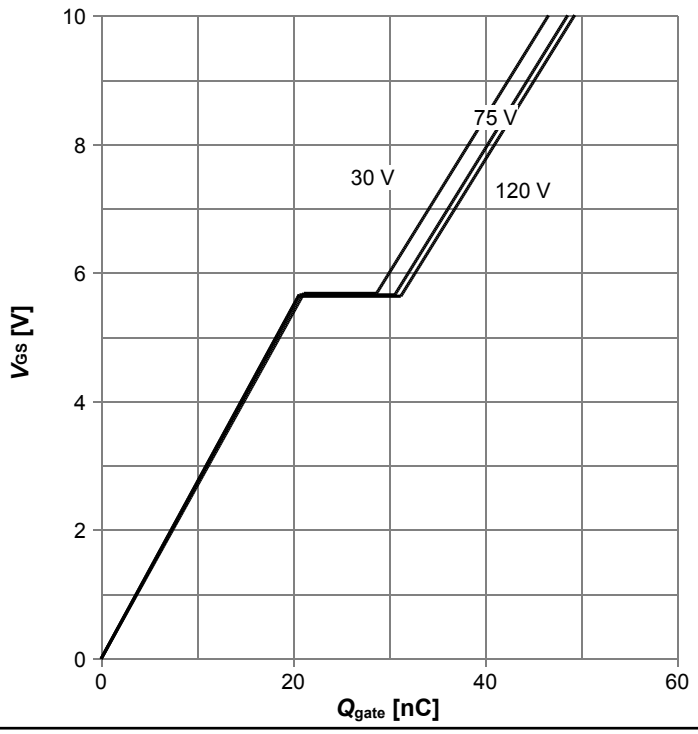
I_F=f(V_{SD}); parameter: T_j

Diagram 13: Avalanche characteristics



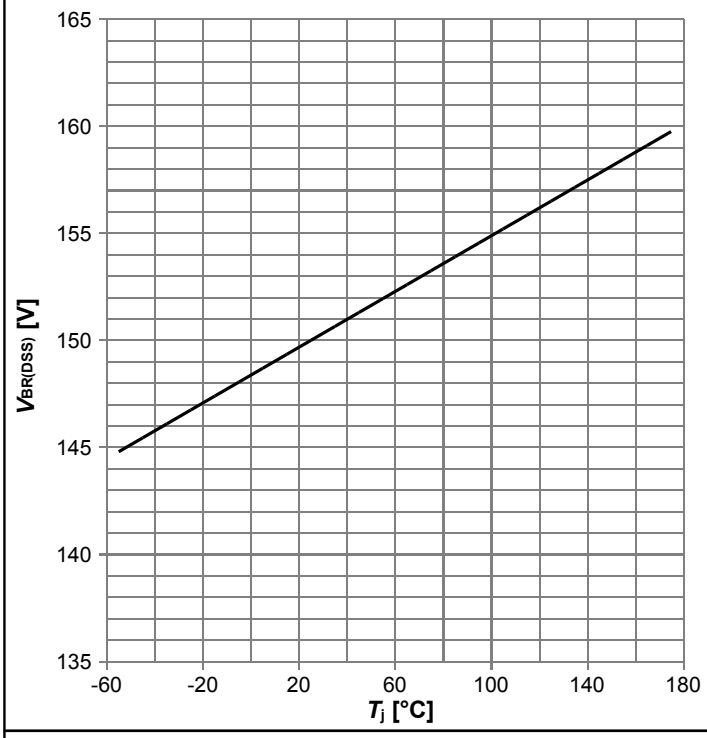
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j(start)}$

Diagram 14: Typ. gate charge



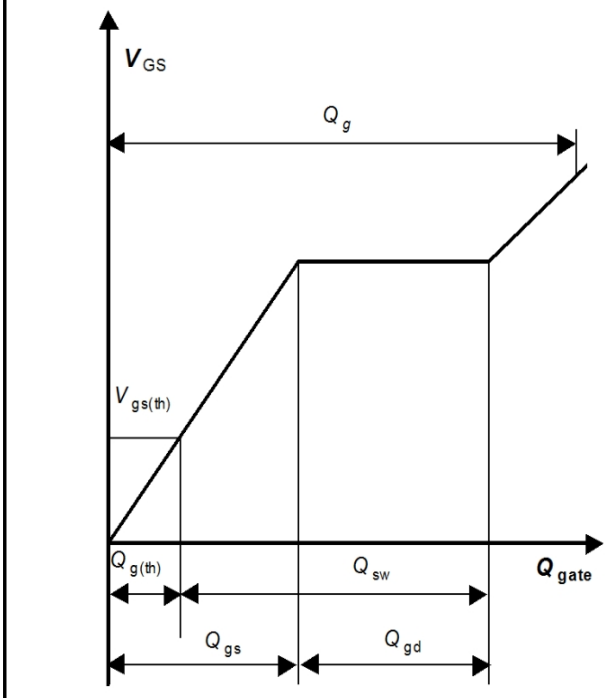
$V_{GS}=f(Q_{gate})$; $I_D=56$ A pulsed; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

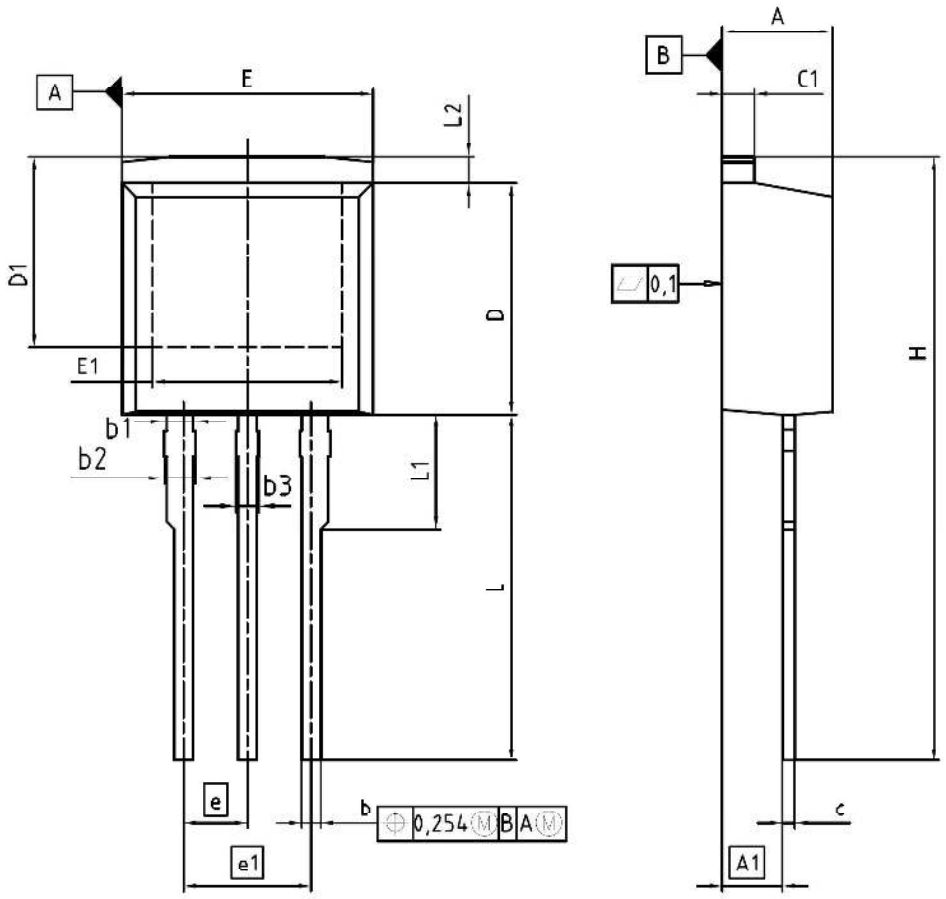


$V_{BR(DSS)}=f(T_j)$; $I_D=1$ mA

Gate charge waveforms



5 Package Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.300	4.572	0.169	0.180
A1	2.150	2.718	0.085	0.107
b	0.650	0.864	0.026	0.034
b1	0.950	1.093	0.037	0.043
b2	0.950	1.400	0.037	0.055
b3	0.650	1.118	0.026	0.044
c	0.330	0.600	0.013	0.024
c1	1.170	1.400	0.046	0.055
D	8.509	9.450	0.335	0.372
D1	6.900	-	0.272	-
E	9.700	10.363	0.382	0.408
E1	6.500	8.600	0.256	0.339
e	2.540		0.100	
e1	5.080		0.200	
N	3		3	
L	13.000	14.000	0.512	0.551
L1	-	4.800	-	0.189
L2	-	1.727	-	0.068

REFERENCE
Z8B00003325

SCALE 0 2.5 0 2.5 5mm

EUROPEAN PROJECTION

ISSUE DATE
05-05-2006

REVISION
03

Figure 1 Outline PG-TO262-3, dimensions in mm/inches

Revision History

IPI076N15N5

Revision: 2016-03-03, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2016-03-03	Release of final version

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